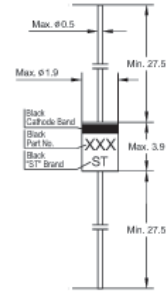


Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- High reliability



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	1N914: 75 1N914A / B: 200	mA
Forward Continuous Current	I_{FM}	1N914: 150 1N914A / B: 300	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$: 1 1N914 at $t = 1\text{ }\mu\text{s}$: 1 1N914A / B at $t = 1\text{ }\mu\text{s}$: 4	A
Power Dissipation	P_{tot}	500	mW
Operating and Storage Temperature Range	T_J, T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit			
Forward Voltage	V_F	-	-	V			
at $I_F = 5\text{ mA}$					1N914B	0.62	0.72
at $I_F = 100\text{ mA}$					1N914B	-	1
at $I_F = 10\text{ mA}$					1N914	-	1
at $I_F = 20\text{ mA}$	1N914A	-	1				
Reverse Current	I_R	-	-	nA μA μA			
at $V_R = 20\text{ V}$					25		
at $V_R = 75\text{ V}$					5		
at $V_R = 20\text{ V}, T_J = 150\text{ }^\circ\text{C}$	50						
Diode Capacitance	C_j	-	4	pF			
Reverse Recovery Time	t_{rr}	-	4	ns			
at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}, V_R = 6\text{ V}, R_L = 100\text{ }\Omega$							